



N 沟道增强型场效应晶体管
N-CHANNEL MOSFET

JCS4N80H

主要参数 MAIN CHARACTERISTICS

ID	4 A
V _{DSS}	800 V
R _{dson-max} (@V _{GS} =10V)	2.5 Ω
Q _{G-typ}	14nC

用途

- 高频开关电源
 - 电子镇流器
 - LED 电源
- APPLICATIONS**
- High frequency switch mode power supply
 - Electronic ballasts
 - LED power supply

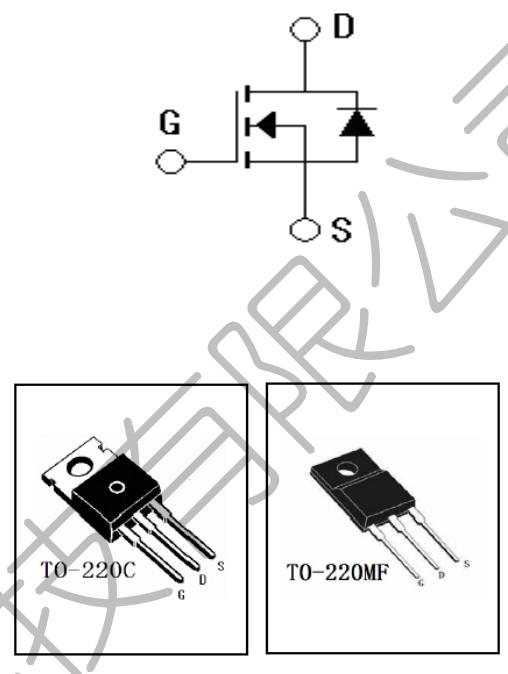
产品特性

- 低栅极电荷
- 低 C_{rss} (典型值 9pF)
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

FEATURES

- Low gate charge
- Low C_{rss} (typical 9pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes	印 记 Marking	封 装 Package	无卤素 Halogen Free	包 装 Packaging	器件重量 Device Weight
JCS4N80CH-O-C-N-B	JCS4N80CH	TO-220C	否 NO	条管 Tube	2.15 g(typ)
JCS4N80FH-O-F-N-B	JCS4N80FH	TO-220MF	否 NO	条管 Tube	2.20 g(typ)





JCS4N80H

绝对最大额定值 ABSOLUTE RATINGS ($T_c=25^\circ\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value		单 位 Unit
		JCS4N80CH	JCS4N80FH	
最高漏极—源极直流电压 Drain-Source Voltage	V_{DSS}	800		V
连续漏极电流 Drain Current -continuous	I_D $T=25^\circ\text{C}$ $T=100^\circ\text{C}$	4	4*	A
		2.5	2.5*	A
最大脉冲漏极电流 (注 1) Drain Current - pulse (note 1)	I_{DM}	16	16*	A
最高栅源电压 Gate-Source Voltage	V_{GSS}	± 30		V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	E_{AS}	230		mJ
雪崩电流 (注 1) Avalanche Current (note 1)	I_{AR}	4		A
重复雪崩能量 (注 1) Repetitive Avalanche Energy (note 1)	E_{AR}	11.0		mJ
二极管反向恢复最大电压变化 速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	4.5		V/ns
耗散功率 Power Dissipation	P_D $T_c=25^\circ\text{C}$ -Derate above 25°C	100	33	W
		1.28	0.43	W/ $^\circ\text{C}$
最高结温及存储温度 Operating and Storage Temperature Range	T_J , T_{STG}	-55~+150		$^\circ\text{C}$
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300		$^\circ\text{C}$

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature





JCS4N80H

电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off -Characteristics						
漏—源击穿电压 Drain-Source Voltage	V_{DSS}	$I_D=250\mu A, V_{GS}=0V$	800	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta V_{DSS}/\Delta T_J$	$I_D=250\mu A$, referenced to $25^\circ C$	-	0.81	-	$V/^\circ C$
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=800V, V_{GS}=0V, T_C=25^\circ C$	-	-	10	μA
		$V_{DS}=640V, T_C=125^\circ C$	-	-	100	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=2.0A$	-	2.0	2.5	Ω
正向跨导 Forward Transconductance	g_{fs}	$V_{DS}=40V, I_D=2.0A$ (note 4)	-	4.6	-	S
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V, f=1.0MHz$	-	1320	1716	pF
输出电容 Output capacitance	C_{oss}		-	105	136	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	9	12	pF



吉林华微电子股份有限公司

JILIN SINO-MICROELECTRONICS CO., LTD.



电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics							
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=400V, I_D=4A, R_G=25\Omega$ (note 4, 5)	-	34	75	ns	
上升时间 Turn-On rise time	t_r		-	85	155	ns	
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	56	113	ns	
下降时间 Turn-Off Fall time	t_f		-	59	118	ns	
栅极电荷总量 Total Gate Charge	Q_g	$V_{DS}=640V, I_D=4A$ $V_{GS}=10V$ (note 4, 5)	-	14	19	nC	
栅一源电荷 Gate-Source charge	Q_{gs}		-	5	-	nC	
栅一漏电荷 Gate-Drain charge	Q_{gd}		-	6	-	nC	
漏一源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings							
正向最大连续电流	I_S		-	-	4	A	
Maximum Continuous Drain-Source Diode Forward Current	I_S		-	-	16	A	
正向最大脉冲电流	I_{SM}		-	-	16	A	
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	-	16	A	
正向压降	V_{SD}	$V_{GS}=0V, I_S=4A$	-	-	1.4	V	
Drain-Source Diode Forward Voltage			-	-	1.4	V	
反向恢复时间	t_{rr}	$V_{GS}=0V, I_S=4A$	-	625	-	ns	
Reverse recovery time	t_{rr}		-	6.71	-	μC	
反向恢复电荷	Q_{rr}	$dI_F/dt=100A/\mu s$ (note 4)	-	-	-	μC	
Reverse recovery charge			-	-	-	μC	

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最 大 Max		单 位 Unit
		JCS4N80CH	JCS4N80FH	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	0.78	2.3	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	62.5	62.5	°C/W

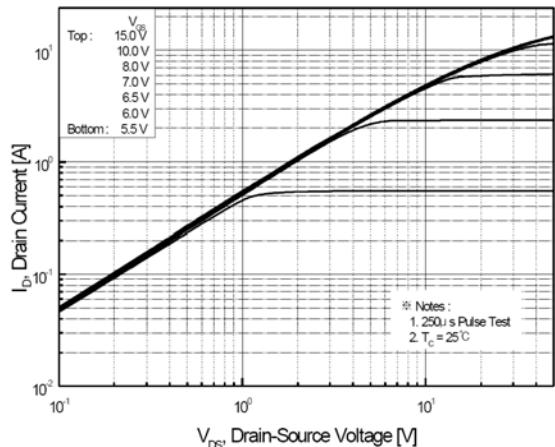
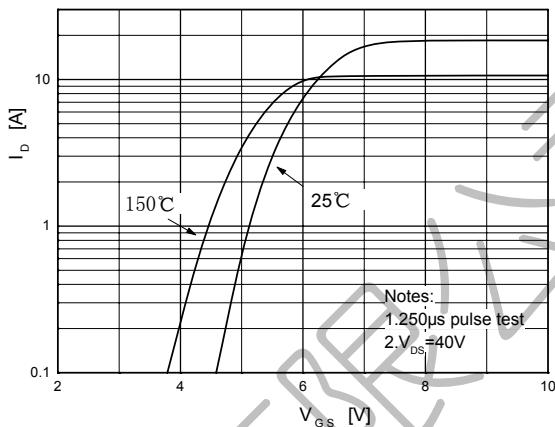
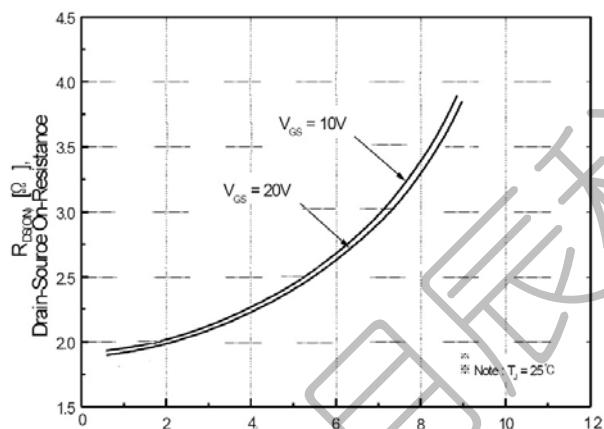
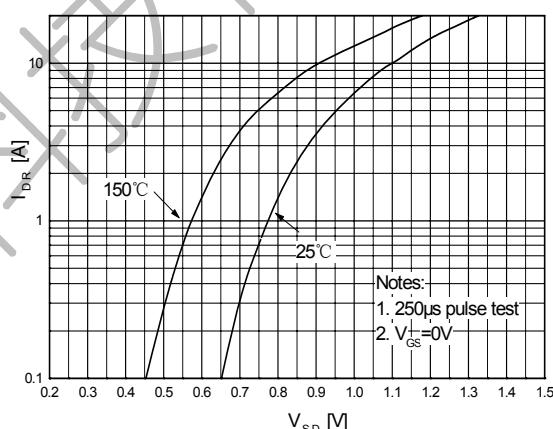
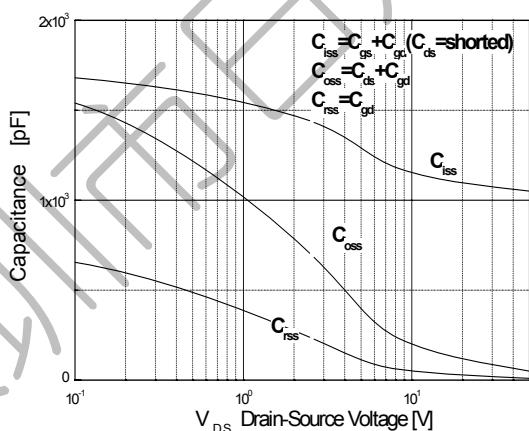
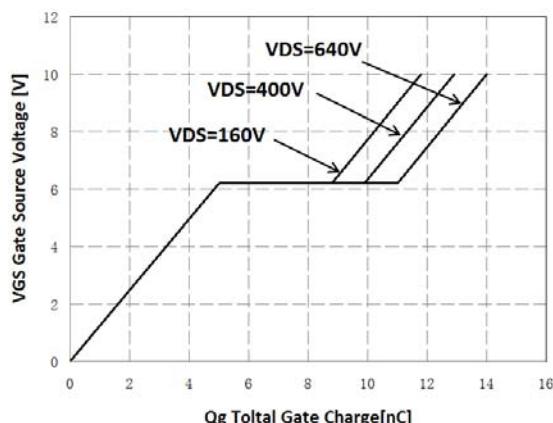
Notes:

注释:

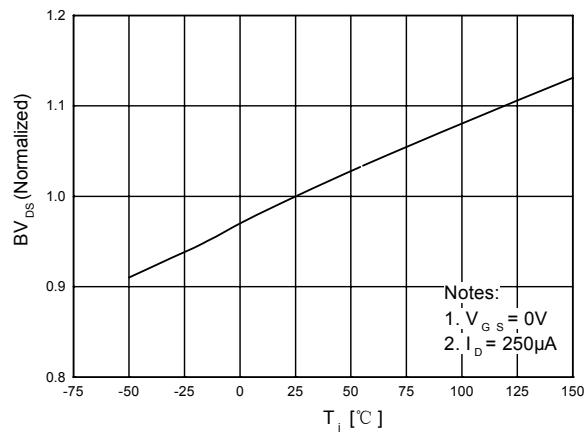
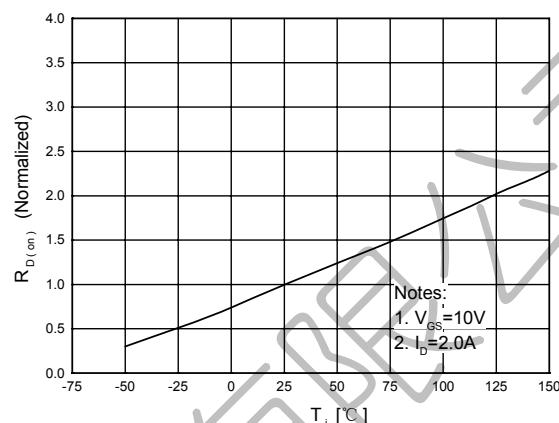
- 1: 脉冲宽度由最高结温限制
 2: $L=40.0mH, I_{AS}=4A, V_{DD}=50V, R_G=25\Omega$, 起始结温 $T_J=25^\circ C$
 3: $I_{SD} \leq 4A, di/dt \leq 200A/\mu s, VDD \leq BV_{DSS}$, 起始结温 $T_J=25^\circ C$
 4: 脉冲测试: 脉冲宽度 $\leq 300\mu s$, 占空比 $\leq 2\%$
 5: 基本与工作温度无关

- 1: Pulse width limited by maximum junction temperature
 2: $L=40.0mH, I_{AS}=4A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^\circ C$
 3: $I_{SD} \leq 4A, di/dt \leq 200A/\mu s, VDD \leq BV_{DSS}$, Starting $T_J=25^\circ C$
 4: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
 5: Essentially independent of operating temperature

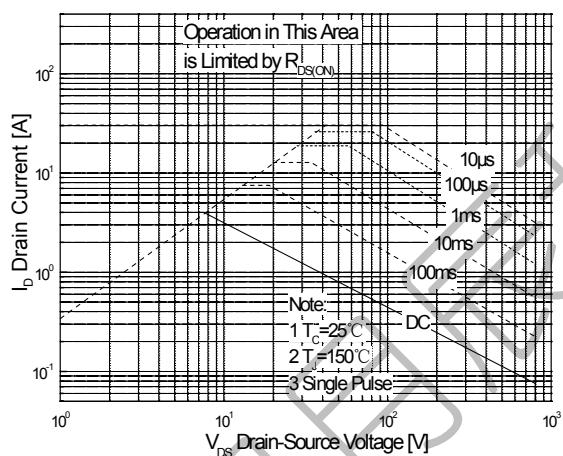
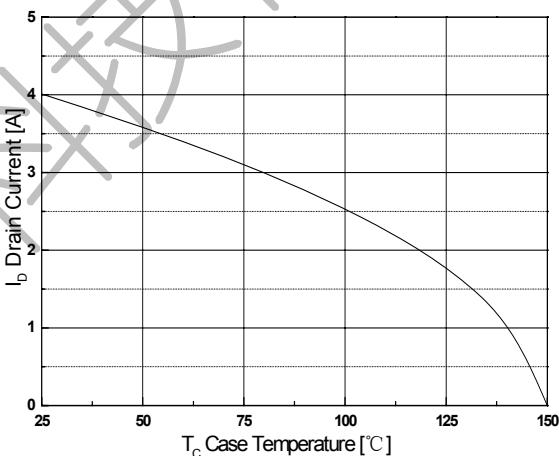


特征曲线 ELECTRICAL CHARACTERISTICS (curves)
On-Region Characteristics

Transfer Characteristics

**On-Resistance Variation vs.
Drain Current and Gate Voltage**

**Body Diode Forward Voltage Variation
vs. Source Current and Temperature**

Capacitance Characteristics

Gate Charge Characteristics


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Breakdown Voltage Variation
vs. TemperatureOn-Resistance Variation
vs. Temperature

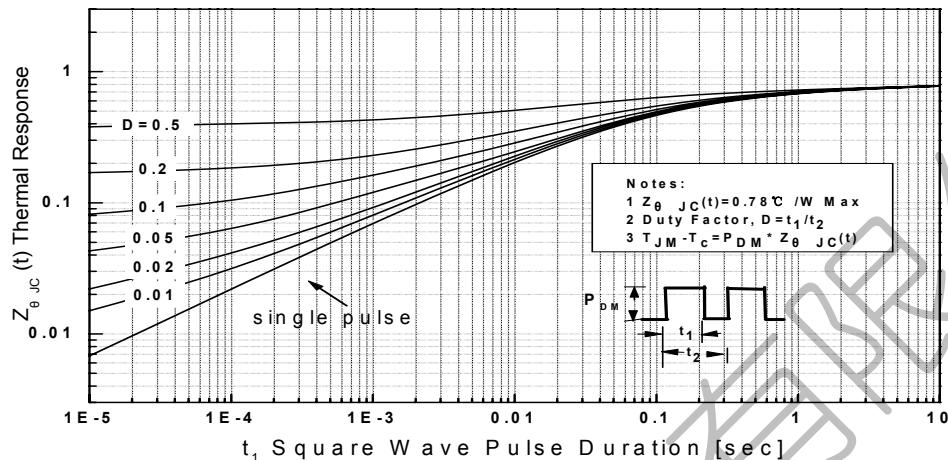
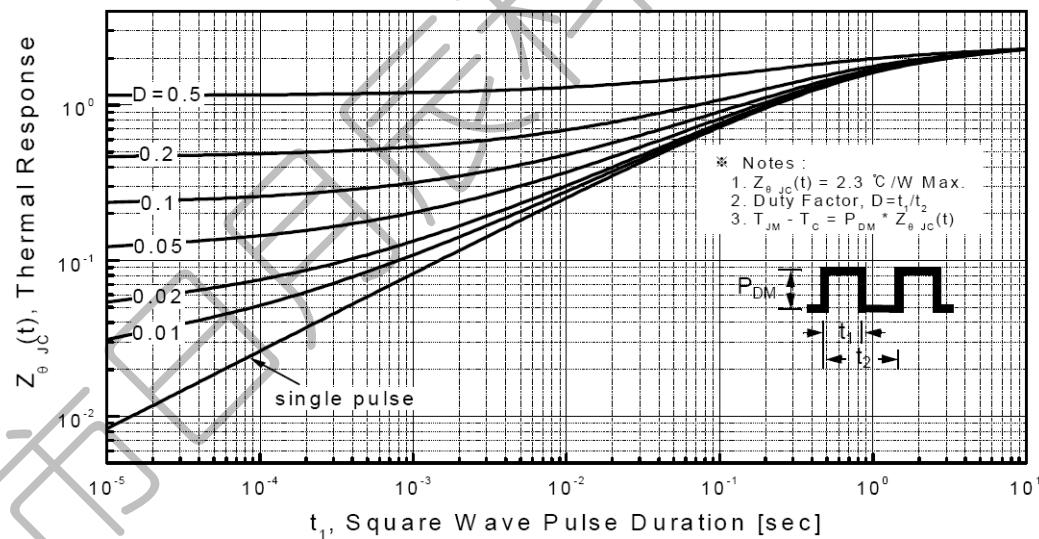
Maximum Safe Operating Area

Maximum Drain Current
vs. Case Temperature



JCS4N80H

特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Transient Thermal Response Curve
JCS4N80CHTransient Thermal Response Curve
JCS4N80FH

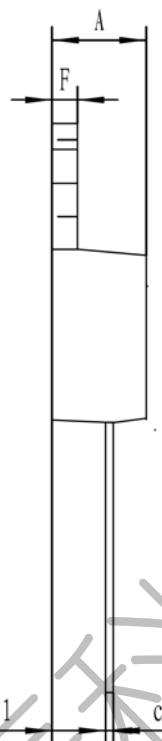
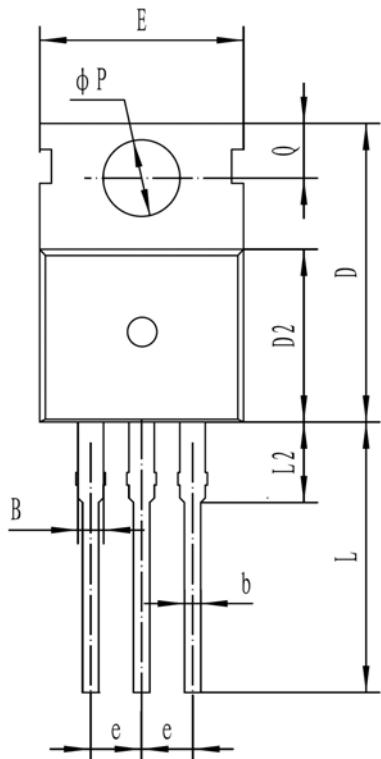


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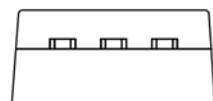
外形尺寸 PACKAGE MECHANICAL DATA

TO-220C

单位 Unit: mm



符号 symbol	MIN	MAX
A	4.30	4.70
B	1.10	1.40
b	0.70	0.95
c	0.40	0.65
D	15.20	16.20
D2	9.00	9.40
E	9.70	10.10
e	2.39	2.69
F	1.25	1.40
L	12.60	13.60
L2	2.80	3.20
Q	2.60	3.00
Q1	2.20	2.60
P	3.50	3.80



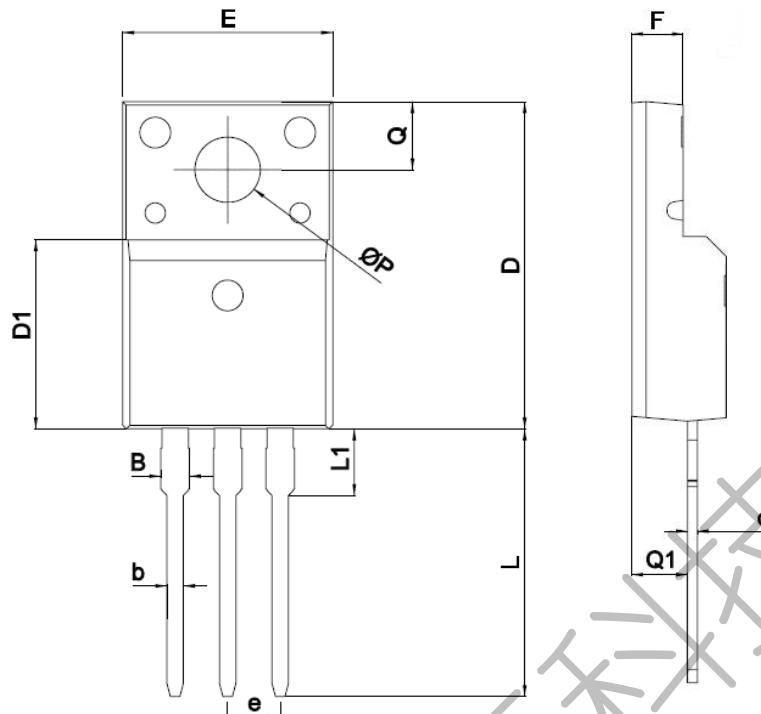


JCS4N80H

外形尺寸 PACKAGE MECHANICAL DATA

TO-220MF

单位 Unit: mm



SYMBOL	mm	
	MIN	MAX
A	4.5	4.9
B		1.47
b	0.7	0.9
c	0.45	0.60
D	15.67	16.07
D1	9.04	9.20
e	2.54TYPE	
E	9.96	10.36
F	2.34	2.74
L	12.58	13.38
L1	3.13	3.33
Q	3.2	3.4
Q1	2.56	2.96
ΦP	3.08	3.28





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